

Form 1449*	Atty. Docket No.: 303.324US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown

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U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
JP	4,460,670	07/01/1984	Ogawa, et al.	430	57	11/19/82
JP	4,462,150	07/31/1984	Nishimura, H., et al.	29	576 B	09/16/82
JP	4,507,673	03/26/1985	Aoyama, M., et al.	357	23 R	09/21/83
JP	4,657,699	04/01/1987	Nair	252	513	12/17/84
JP	4,738,729	04/01/1998	Yoshida, et al.	136	258	01/27/87
JP	4,768,072	08/30/1988	Seki, Y., et al.	357	29	10/02/86
JP	4,769,686	09/06/1988	Horiuchi, M., et al.	357	23.8	06/19/87
JP	4,841,349	06/20/1989	Nakano, M.	357	30	10/28/87
JP	4,849,797	07/18/1989	Ukai, Y., et al.	357	237	01/20/88
JP	4,893,273	01/09/1990	Usami	365	185	03/21/86
JP	5,049,950	09/17/1991	Fujii, Y., et al.	357	2	08/09/90
JP	5,111,430	05/05/1992	Morie	365	185	06/21/90
JP	5,145,741	09/01/1992	Quick	428	402	02/28/91
JP	5,235,195	08/10/1993	Tran, N.T., et al.	257	59	10/19/92
JP	5,260,593	11/09/1993	Lee, R.R.	257	316	12/10/91
JP	5,293,560	03/08/1994	Harari, E.	365	185	11/03/92
JP	5,298,796	03/29/1994	Tawel, R.	307	201	07/08/92
JP	5,369,040	11/29/1994	Halvis, et al.	437	3	04/12/93
JP	5,371,383	12/06/1994	Miyata, K., et al.	257	77	05/14/93
JP	5,407,845	04/18/1995	Nasu, Y., et al.	437	40	10/13/93
JP	5,415,126	05/16/1995	Loboda, M.J., et al.	117	88	08/16/93
JP	5,449,941	09/12/1995	Yamazaki, S., et al.	257	411	10/27/92
JP	5,455,432	10/03/1995	Hartsell, M.L., et al.	257	77	10/11/94
JP	5,465,249	11/07/1995	Cooper, et al.	365	149	11/26/91
JP	5,477,485	12/19/1995	Bergemont, et al.	365	185.24	02/22/95
JP	5,508,543	04/16/1996	Hartstein, A.M., et al.	257	314	04/29/94
JP	5,530,581	06/25/1996	Cogan	359	265	05/31/95
JP	5,557,114	09/17/1996	Leas, J.M., et al.	257	59	01/12/95
JP	5,562,769	10/08/1996	Dreifus, D.L., et al.	117	86	02/22/95
JP	5,580,380	12/03/1996	Liu, et al.	117	86	01/30/95
JP	5,604,357	02/18/1997	Hori, T.	257	24	07/11/95
JP	5,623,442	04/22/1997	Gotou, H., et al.	365	185.08	06/08/94
JP	5,629,222	05/13/1997	Yamazaki, S., et al.	438	259	04/28/95
JP	5,654,208	08/05/1997	Harris, C., et al.	438	522	05/08/95
JP	5,670,790	09/23/1997	Katoh, et al.	257	14	09/19/96
JP	5,714,766	02/03/1998	Chen, et al.	257	20	09/29/95
JP	5,719,410	02/17/1998	Suehiro, S., et al.	257	77	12/16/96
JP	5,740,104	04/14/1998	Forbes, L.	365	185.03	01/29/97

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U.S. PATENT DOCUMENTS

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<i>[Signature]</i>	5,754,477	05/19/1998	Forbes, L.	365	185.33	01/29/97
<i>[Signature]</i>	5,786,250	07/28/1998	Wu, Z., et al.	438	254	03/14/97
<i>[Signature]</i>	5,789,276	08/04/1998	Leas, J.M., et al.	438	59	12/08/95
<i>[Signature]</i>	5,801,401	09/01/1998	Forbes, L.	257	77	01/29/97
<i>[Signature]</i>	5,846,859	12/08/1998	Lee, S.	438	253	02/23/96
<i>[Signature]</i>	5,877,041	03/02/1999	Fuller, R.T.	438	105	06/30/97
<i>[Signature]</i>	5,886,368	03/23/1999	Forbes, L., et al.	257	77	07/29/97
<i>[Signature]</i>	5,886,379	03/23/1999	Jeong, H.	257	319	01/27/97
<i>[Signature]</i>	5,898,197	04/27/1999	Fujiwara, H.	257	317	06/03/97
<i>[Signature]</i>	5,907,775	05/25/1999	Tseng, H.	438	261	04/11/97
<i>[Signature]</i>	6,018,166	01/25/2000	Lin, K., et al.	257	22	07/30/98
<i>[Signature]</i>	6,031,263	02/29/2000	Forbes, L., et al.	257	315	07/29/97
<i>[Signature]</i>	6,034,001	03/07/2000	Shor, J.S., et al.	438	931	02/17/94
<i>[Signature]</i>	6,075,259	06/13/2000	Baliga, B.J.	257	77	07/13/99

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
<i>[Signature]</i>	03-222367	10/01/1991	Japan	H01L	29/784	
<i>[Signature]</i>	06-224431	08/12/1994	Japan	H01L	29/784	
<i>[Signature]</i>	06-302828	10/28/1994	Japan	H01L	29/788	
<i>[Signature]</i>	07-226507	08/22/1995	Japan	H01L	29/78	
<i>[Signature]</i>	08-255878	10/01/1996	Japan	H01L	27/10	
<i>[Signature]</i>	08-255878-TR	10/01/1996	Japan	H01L	27/10	
<i>[Signature]</i>	60-184681	09/20/1985	Japan	C23C	16/30	
<i>[Signature]</i>	60-242678	12/02/1985	Japan	H01L	29/73	

OTHER DOCUMENTS

**Examiner Initial	(Including Author, Title, Date, Pertinent Pages, Etc.)
<i>[Signature]</i>	Akasaki, I., et al., "Effects of AlN Buffer Layer on Crystallographic Structure and on Electrical and Optical Properties of GaN and Ga(1-x)Al(x)N [0 < x (< or =) 0.4] Films Grown on Sapphire Substrate by MOVPE", <u>J. Crystal Growth</u> , 98, 209-219, (1989)
<i>[Signature]</i>	Alok, D., et al., "Electrical Properties of Thermal Oxide Grown on N-type 6H-Silicon Carbide", <u>Applied Physics Letters</u> , 64, 2845-2846, (May 23, 1994)

Examiner <i>J. Mondt</i>	Date Considered <i>05/12/02</i>
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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

- JLF* Andrieux, M., et al., "Interface and Adhesion of PACVD SiC Based Films on Metals", Supp. "Le Vide: science, technique et applications, 279, 212-214, (1996)
- JLF* Bachmann, P., et al., "Influence on Surface Modifications on the Electronic Properties of CVD Diamond Films", Diamond and Related Materials, 5, 1378-1383, (1996)
- JLF* Baglee, D., "Characteristics & Reliability of 100 Angstrom Oxides", IEEE 22nd Annual Proc.: Reliability Physics, Las Vegas, 152-155, (April 3-5, 1984)
- JLF* Beheim, G., et al., "Magnetron Plasma Etching of SiC for Microstructures", Proc: SPIE - Integrated Optics and Microstructures III, San Jose, CA, 82-86, (Jan 29, 1996)
- JLF* Bengtsson, S., et al., "Applications of Aluminum Nitride Films Deposited by Reactive Sputtering to Silicon-On-Insulator Materials", Japanese J. Applied Physics, 35, 4175-4181, (1996)
- JLF* Benjamin, M., et al., "UV Photoemission Study of Heteroepitaxial AlGaIn Films Grown on 6H-SiC", Applied Surface Science, 104/105, 455-460, (1996)
- JLF* Bermudez, V., et al., "The Growth and Properties of Al and AlN Films on GaN(0001)-(1 x 1)", J. Applied Physics, 79, 110-119, (Jan. 1996)
- JLF* Casey, H., et al., "Low Interface Trap Density for Remote Plasma Deposited SiO₂ on n-type GaN", Applied Phys. Lett., 68, 1850-1852, (March 1996)
- JLF* Chang, C., et al., "Novel Passivation Dielectrics-The Boron- or Phosphorus-Doped Hydrogenated Amorphous Silicon Carbide Films", Journal of the Electrochemical Society, 132, 418-422, (Feb. 1985)
- JLF* Choi, J., et al., "Effect of Deposition Conditions and Pretreatments on the Microstructure of MPECVD Diamond Thin Films", Materials Chemistry and Physics, 45, 176-179, (1996)
- JLF* Clarke, G., et al., "The Infrared Properties of Magnetron-Sputtered Diamond-Like Thin Films", Thin Solid Films, 280, 130-135, (1996)
- JLF* Compagnini, G., et al., "Spectroscopic Characterization of Annealed Si(1-x)C(x) Films", J. Materials Res., 11, 2269-2273, (Sept. 1996)

Examiner <u>J. MONDT</u> <i>[Signature]</i>	Date Considered <u>11/05/02</u>
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*Substitute Disclosure Statement Form (PTO 729)

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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

<i>JLF</i>	Dartnell, N., et al., "Reactive Ion Etching of Silicon Carbide (Si(x)C(1-x))", <u>Vacuum</u> , 46, 349-355, (1995)
<i>JLF</i>	Demichelis, F., et al., "Influence of Doping on the Structural and Optoelectronic Properties of Amorphous and Microcrystalline Silicon Carbide", <u>Journal of Applied Physics</u> , 72, 1327-1333, (Aug. 15, 1992)
<i>JLF</i>	Demichelis, F., et al., "Physical Properties of Undoped and Doped Microcrystalline SiC:H Deposited By PECVD", <u>Materials Research Society Symposium Proceedings</u> , 219, Anaheim, CA, 413-418, (4/30 - 5/3, 1991)
<i>JLF</i>	Dipert, B., et al., "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30, 48-52, (October 1993)
<i>JLF</i>	Fissel, A., et al., "Epitaxial Growth of SiC Thin Films on Si-stabilized alpha-SiC (0001) at Low Temperatures by Solid-source Molecular Beam Epitaxy", <u>Journal of Crystal Growth</u> , 154, 72-80, (1995)
<i>JLF</i>	Friedrichs, P., et al., "Interface Properties of Metal-Oxide-Semiconductor Structures on N-Type 6H and 4H-SiC", <u>J. Applied Physics</u> , 79, 7814-7819, (May 15, 1996)
<i>JLF</i>	Fujii, T., et al., "Bonding Structures in Highly Photoconductive a-SiC:H Films Deposited by Hybrid-Plasma Chemical Vapor Deposition", <u>Journal of Non-Crystalline Solids</u> , 198-200, 577-581, (1996)
<i>JLF</i>	Goetzberger, A., et al., <u>Applied Solid State Science: Advances in Materials and Device Research</u> , R. Wolfe, ed., Academic Press, New York, Including pg. 233, (1969)
<i>JLF</i>	Graul, J., et al., "Growth Mechanism of Polycrystalline beta-SiC Layers on Silicon Substrate", <u>Applied Phys. Lett.</u> , 21, 67-69, (July 1972)
<i>JLF</i>	Hamakawa, Y., et al., "Optoelectronics and Photovoltaic Applications of Microcrystalline SiC", <u>Materials Research Society Symposium Proceedings</u> , 164, Boston, MA, 291-301, (11/29-12/1, 1989)
<i>JLF</i>	He, Z., et al., "Ion-beam-assisted Deposition of Si-carbide Films", <u>Thin Solid Films</u> , 260, 32-37, (1995)

Examiner <i>J. MONDT</i>	Date Considered <i>11/05/02</i>
--------------------------	---------------------------------

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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

JH Hu, G., et al., "Will Flash Memory Replace Hard Disk Drive?", 1994 IEEE International Electron Device Meeting, Panel Discussion, Session 24, Outline, 2 pages, (Dec. 1994)

JH Hwang, J., et al., "High Mobility beta-SiC Epilayer Prepared by Low-pressure Rapid Thermal Chemical Vapor Deposition on a (100) Silicon Substrate", Thin Solid Films, 272, 4-6, (1996)

JH Jou, S., et al., "Electron Emission Characterization of Diamond Thin Films Grown from a Solid Carbon Source", Thin Solid Films, 280, 256-261, (1996)

JH Kothandaraman, M., et al., "Reactive Ion Etching of Trenches in 6H-SiC", J. Electronic Materials, 25, 875-878, (1996)

JH Kumbhar, A., et al., "Growth of Clean Amorphous Silicon-Carbon Alloy Films by Hot-Filament Assisted Chemical Vapor Deposition Technique", Applied Phys. Lett., 66, 1741-1743, (April 1995)

JH Lakshmi, E., et al., "Interface-State Characteristics of GaN/GaAs MIS Capacitors", Solid-State Electronics, 25, 811-815, (1982)

JH Lanois, F., et al., "Angle Etch Control for Silicon Carbide Power Devices", Applied Phys. Lett., 69, 236-238, (July 1996)

JH Lau, S., et al., "Optoelectronic Properties of Highly Conductive Microcrystalline SiC Produced by Laser Crystallization of Amorphous SiC", J. of Non-Crystalline Solids, 198-200, 907-910, (1996)

JH Leggieri, G., et al., "Laser Ablation Deposition of Silicon Carbide Films", Applied Surface Science, 96-98, 866-869, (1996)

JH Lei, T., et al., "Epitaxial Growth and Characterization of Zinc-Blende Gallium Nitride on (001) Silicon", J. Appl. Phys., 71, 4933-4943, (May 1992)

JH Liu, J., et al., "Formation of SiC Films on Silicon Field Emitters", Materials Res. Soc. Symp. Proc., 311, San Francisco, CA, (April 13-15, 1993)

JH Liu, J., et al., "Modification of Si Field Emitter Surfaces by Chemical Conversion to SiC", J. Vac. Sci. Technology, B 12, 717-721, (1994)

JH Luo, J., et al., "Localized Epitaxial Growth of Hexagonal and Cubic SiC Films on Si by Vacuum Annealing", Applied Phys. Lett., 69, 916-918, (Aug. 1996)

Examiner

J. MONDT *JH*

Date Considered

11/05/02

*Substitute Disclosure Statement Form (PTO-1449)



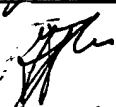
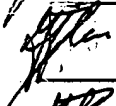
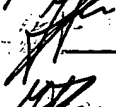

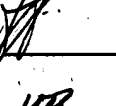
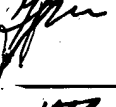
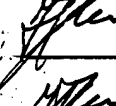
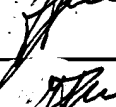
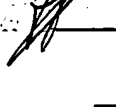
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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

	Martins, R., et al., "Transport Properties of Doped Silicon Oxycarbide Microcrystalline Films Produced by Spatial Separation Techniques", <u>Solar Energy Materials and Solar Cells</u> , 41-42, 493-517, (1996)
	Martins, R., et al., "Wide Band Gap Microcrystalline Silicon Thin Films", <u>Diffusion and Defect Data : Solid State Phenomena</u> , 44-46, Part 1, Scitec Publications, 299-346, (1995)
	Maurry, F., et al., "Chemical Vapor Co-Deposition of C and SiC at Moderate Temperature for the Synthesis of Compositionally Modulated Si(x)C(1-x) Ceramic Layers", <u>Surface and Coatings Technology</u> , 76-77, 119-125, (1995)
	McLane, G., et al., "High Etch Rates of SiC in Magnetron Enhanced SF(6) Plasmas", <u>Applied Phys. Lett.</u> , 68, 3755-3757, (June 1996)
	Mogab, C., et al., "Conversion of Si to Epitaxial SiC by Reaction with C(2)H(2)", <u>J. Applied Physics</u> , 45, 1075-1084, (March 1974)
	Molnar, R., et al., "Growth of Gallium Nitride by Electron-Cyclotron Resonance Plasma-Assisted Molecular-Beam Epitaxy: The Role of Charged Species", <u>J. Appl. Phys.</u> , 76, 4587-4595, (1994)
	Muller, K., et al., "Trench Storage Node Technology for Gigabit DRAM Generations", <u>Digest IEEE International Electron Devices Meeting</u> , San Francisco, CA, 507-510, (Dec. 1996)
	Nemanich, P., et al., "Diamond Negative Electron Affinity Surfaces, Structures and Devices", <u>Proc. : Third International Conference on Applications of Diamond Films and Related Materials</u> , 1, Gaithersburg, MD, 17-24, (1995)
	Nemanich, R., et al., "Negative Electron Affinity Surfaces of Aluminum Nitride and Diamond", <u>Diamond and Related Materials</u> , 5, 790-796, (1996)
	Ouyang, M., et al., "Deposition of Diamond-Like Carbon Films via Excimer Laser Ablation of Polybutadiene", <u>Materials Science and Engineering</u> , B39, 228-231, (1996)
	Pankove, J., "Photoelectric Emission", <u>In: Optical Processes in Semiconductors</u> , Dover Publications Inc., New York, 287-301, (1971)

Examiner: J. MONDT 	Date Considered: 11/05/02
--	---------------------------

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OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

<i>JFM</i>	Pankove, J., et al., "Photoemission from GaN", <u>Applied Phys. Lett.</u> , 25, 53-55, (1974)
<i>JFM</i>	Papadas, C., et al., "Modeling of the Intrinsic Retention Characteristics of FLOTOX EEPROM Cells Under Elevated Temperature Conditions", <u>IEEE Transaction on Electron Devices</u> , 42, 678-682, (April 1995)
<i>JFM</i>	Patuwathavithane, C., et al., "Oxidation Studies for 6H-SiC", <u>Proc: 4th Int. Conf. on Amorphous and Crystalline Silicon Carbide IV</u> , Santa Clara, CA, 163-169, (Oct. 9-11, 1991)
<i>JFM</i>	Pereyra, I., et al., "Wide Gap a-Si(1-x)C(x): H Thin Films Obtained Under Starving Plasma Deposition Conditions", <u>J. Non-Crystalline Solids</u> , 201, 110-118, (1996)
<i>JFM</i>	Pollack, S., "Electron Transport Through Insulating Thin Films", <u>Appl. Solid-State Science</u> , 1, 345-355, (1969)
<i>JFM</i>	Prendergast, J., "FLASH or DRAM: Memory Choice for the Future", <u>IEEE Electron Device Meeting, Session 25</u> , Phoenix, AZ, (1995)
<i>JFM</i>	Rahman, M., et al., "Preparation and Electrical Properties of An Amorphous SiC/ Crystalline Si p(+)n Heterostructure", <u>Japanese J. Applied Physics</u> , 23, 515-524, (May 1984)
<i>JFM</i>	Renlund, G., et al., "Silicon Oxycarbide Glasses: Part I. Preparation and Chemistry", <u>Journal of Materials Research</u> , 6, 2716-2722, (December 1991)
<i>JFM</i>	Renlund, G., et al., "Silicon Oxycarbide Glasses: Part II. Structure and Properties", <u>Journal of Materials Research</u> , 6, 2723-2734, (December 1991)
<i>JFM</i>	Sakata, I., et al., "Amorphous Silicon/Amorphous Silicon Carbide Heterojunctions Applied to Memory Device Structures", <u>Electronics Letters</u> , 30(9), 688-689, (1994)
<i>JFM</i>	Schmidt, I., et al., "Low Temperature Diamond Growth Using Fluorinated Hydrocarbons", <u>Diamond and Related Materials</u> , 5, 1318-1322, (1996)
<i>JFM</i>	Serre, C., et al., "Ion-Beam Synthesis of Amorphous SiC Films: Structural Analysis and Recrystallization", <u>J. Appl. Phys.</u> , 79, 6907-6913, (May 1996)

Examiner <i>J.M. MONDT</i>	Date Considered <i>11/05/02</i>
----------------------------	---------------------------------

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OTHER DOCUMENTS

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(Including Author, Title, Date, Pertinent Pages, Etc.)

<i>JLF</i>	Sim, S., et al., "A New Planar Stacked Technology (PST) for Scaled and Embedded DRAMs", <u>Digest IEEE Int. Electron Devices Meeting</u> , San Francisco, CA, 504-507, (Dec. 1996)
<i>JLF</i>	Suzaki, Y., et al., "Quantum Size Effects of a-Si(:H)/a-SiC(:H) Multilayer Films Prepared by rf Sputtering", <u>Abstracts of Papers Published in the Int. J. Japanese Soc. for Precision Engineering</u> , 28, Abstract of Paper in vol. 60, 182, (June 1994)
<i>JLF</i>	Svirkova, N., et al., "Deposition Conditions and Density-of-States Spectrum of a-Si(1-x)C(x) :H Films Obtained by Sputtering", <u>Semiconductors</u> , 28, 1164-1169, (Dec. 1994)
<i>JLF</i>	Sze, S., <u>Physics of Semiconductors</u> , 2nd Edition., John Wiley & Sons, Pub., New York, ISBN 0471056618, (1981) <i>Devices JLF</i>
<i>JLF</i>	Sze, S.M., <u>In: Physics of Semiconductor Devices</u> , Wiley-Interscience, New York, p. 496-497, (1969)
<i>JLF</i>	Tarui, Y., "Flash Memory Features Simple Structure, Superior Integration", <u>JEE</u> , 30, 84-87, (Sept. 1993)
<i>JLF</i>	Tenhover, M., et al., "DC-Magnetron Sputtered Silicon Carbide", <u>Materials Res. Soc. Symp. Proc.</u> , 356, Boston, MA, 227-232, (11/28-12/02, 1994)
<i>JLF</i>	Thomas, J., et al., "Plasma Etching and Surface Analysis of a-SiC :H Films Deposited by Low Temperature Plasma Enhanced Chemical Vapor Deposition", <u>Materials Res. Soc. Symp. Proc.</u> , 334, Boston, MA, 445-450, (11/29-12/02, 1993)
<i>JLF</i>	Tiwari, S., et al., "A silicon nanocrystal based memory", <u>Appl. Physics Lett.</u> , 68, 1377-1379, (1996)
<i>JLF</i>	Tiwari, S., et al., "Volatile and Non-Volatile Memories in Silicon with Nano-Crystal Storage", <u>Int'l Electron Devices Meeting: Technical Digest</u> , Washington, DC, 521-524, (Dec. 1995)
<i>JLF</i>	Tucker, C., et al., "Ion-beam-assisted Deposition of Nonhydrogenated a-Si:C Films", <u>Can. J. Physics</u> , 74, 97-101, (1996)

Examiner

J. MONDT

Date Considered

11/05/02

*Substitute Disclosure Statement Form (PTO-1449)


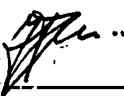
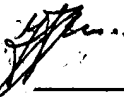
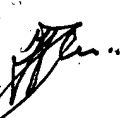
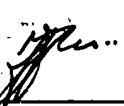
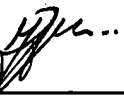
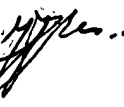
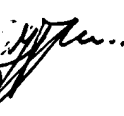
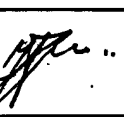
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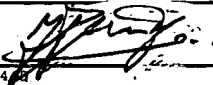
Form 1449*	Atty. Docket No.: 303.324US4	Serial No. Unknown
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	Filing Date: Herewith	Group: Unknown

OTHER DOCUMENTS

**Examiner
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

	van der Weide, J., et al., "Negative-electron-affinity Effects on the Diamond (100) Surface", <u>Physical Review B [Condensed Matter]</u> , <u>50</u> , 5803-5806, (Aug. 15, 1994)
	Vodakov, Y., et al., "Diffusion and Solubility of Impurities in Silicon Carbide", <u>In: Silicon Carbide</u> , R.C. Marshall, et al., eds., Univ. of South Carolina Press, 508-519, (1973)
	Wahab, Q., et al., "3C-SiC / Si / 3C-SiC Epitaxial Trilayer Films Deposited on Si (111) Substrates by Reactive Magnetron Sputtering", <u>J. Materials Res.</u> , <u>10</u> , 1349-1351, (June 1995)
	Watanabe, A., et al., "SiC Thin Film Preparation by ArF Excimer Laser Chemical Vapor Deposition. Part 1: Rate of Photolysis of Alkylsilanes by ArF Excimer Laser and their Decomposition Products", <u>Thin Solid Films</u> , <u>274</u> , 70-75, (1996)
	Wolter, S., et al., "Textured Growth of Diamond on Silicon via in situ Carburization and Bias-Enhanced Nucleation", <u>Appl. Phys. Lett.</u> , <u>62</u> , 1215-1217, (March 1993)
	Wu, K., et al., "The Growth and Characterization of Silicon/Silicon Carbide Heteroepitaxial Films on Silicon Substrates by Rapid Thermal Chemical Vapor Deposition", <u>Japanese J. Appl. Phys.</u> , <u>35</u> , 3836-3840, (1996)
	Yamaguchi, Y., et al., "Properties of Heteroepitaxial 3C-SiC Films Grown by LPCVD", <u>Digest of Tech. Papers: 8th Int. Conf. on Solid-State Sensors and Actuators and Eurosensors IX</u> , vol. <u>2</u> , Stockholm, Sweden, 190-193, (June 1995)
	Yamanashi, H., et al., "Deposition of Silicon Compound Thin Films in DC Discharge Plasma Using Hydrogen-Hexamethyldisilane Gas Mixture", <u>Proc.: Int. Symp. on Surfaces and Thin Films of Electronic Materials. Bull. of the Res. Institute of Electronics, Shizuoka University</u> , <u>30</u> , 95-98, (1995)
	Yee, A., et al., "The Effect of Nitrogen on Pulsed Laser Deposition of Amorphous Silicon Carbide Films: Properties and Structure", <u>J. Materials Research</u> , <u>11</u> , 1979-1986, (1996)

Examiner <u>J. MONDI</u> 	Date Considered <u>7/05/02</u>
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*Substitute Disclosure Statement Form (PTO-1449)

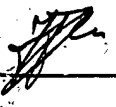
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OTHER DOCUMENTS

**Examiner
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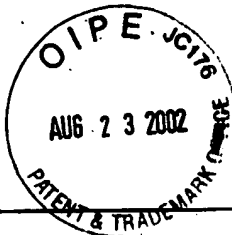
(Including Author, Title, Date, Pertinent Pages, Etc.)

 Yoder, M., "Wide Bandgap Semiconductor Materials and Devices", IEEE
Transactions on Electron Devices, 43, 1633-1636, (October 1996)

Examiner <u>J. MONDT</u>	Date Considered <u>11/05/02</u>
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*Substitute Disclosure Statement Form (Pgs-1445)

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U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
JP	5,754,477	05/19/1998	Forbes, L.	365	185.33	01/29/97
JP	5,786,250	07/28/1998	Wu, Z., et al.	438	254	03/14/97
JP	5,789,276	08/04/1998	Leas, J.M., et al.	438	59	12/08/95
JP	5,801,401	09/01/1998	Forbes, L.	257	77	01/29/97
JP	5,846,859	12/08/1998	Lee, S.	438	253	02/23/96
JP	5,877,041	03/02/1999	Fuller, R.T.	438	105	06/30/97
JP	5,886,368	03/23/1999	Forbes, L., et al.	257	77	07/29/97
JP	5,886,379	03/23/1999	Jeong, H.	257	319	01/27/97
JP	5,898,197	04/27/1999	Fujiwara, H.	257	317	06/03/97
JP	5,907,775	05/25/1999	Tseng, H.	438	261	04/11/97
JP	6,018,166	01/25/2000	Lin, K., et al.	257	22	07/30/98
JP	6,031,263	02/29/2000	Forbes, L., et al.	257	315	07/29/97
JP	6,034,001	03/07/2000	Shor, J.S., et al.	438	931	02/17/94
JP	6,075,259	06/13/2000	Baliga, B.J.	257	77	07/13/99

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes	No
JP	03-222367	10/01/1991	Japan	H01L	29/784		
JP	06-224431	08/12/1994	Japan	H01L	29/784		
JP	06-302828	10/28/1994	Japan	H01L	29/788		
JP	07-226507	08/22/1995	Japan	H01L	29/78		
JP	08-255878	10/01/1996	Japan	H01L	27/10		
JP	08-255878-TR	10/01/1996	Japan	H01L	27/10		
JP	60-184681	09/20/1985	Japan	C23C	16/30		
JP	60-242678	12/02/1985	Japan	H01L	29/73		

OTHER DOCUMENTS

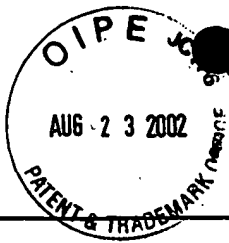
(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner Initial	
JP	Akasaki, I., et al., "Effects of AlN Buffer Layer on Crystallographic Structure and on Electrical and Optical Properties of GaN and Ga(1-x)Al(x)N [0 < x (< or =) 0.4] Films Grown on Sapphire Substrate by MOVPE", <u>J. Crystal Growth</u> , 98, 209-219, (1989)
JP	Alok, D., et al., "Electrical Properties of Thermal Oxide Grown on N-type 6H-Silicon Carbide", <u>Applied Physics Letters</u> , 64, 2845-2846, (May 23, 1994)

Examiner <u>J. MONDT</u>	Date Considered <u>5/12/02</u>
--------------------------	--------------------------------

*Substitute Disclosure Statement Form (PTO-1449)

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OTHER DOCUMENTS
(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner Initial

	Andrieux, M., et al., "Interface and Adhesion of PACVD SiC Based Films on Metals", <u>Supp. "Le Vide: science, technique et applications</u> , 279, 212-214, (1996)
	Bachmann, P., et al., "Influence on Surface Modifications on the Electronic Properties of CVD Diamond Films", <u>Diamond and Related Materials</u> , 5, 1378-1383, (1996)
	Baglee, D., "Characteristics & Reliability of 100 Angstrom Oxides", <u>IEEE 22nd Annual Proc.: Reliability Physics</u> , Las Vegas, 152-155, (April 3-5, 1984)
	Beheim, G., et al., "Magnetron Plasma Etching of SiC for Microstructures", <u>Proc: SPIE - Integrated Optics and Microstructures III</u> , San Jose, CA, 82-86, (Jan 29, 1996)
	Bengtsson, S., et al., "Applications of Aluminum Nitride Films Deposited by Reactive Sputtering to Silicon-On-Insulator Materials", <u>Japanese J. Applied Physics</u> , 35, 4175-4181, (1996)
	Benjamin, M., et al., "UV Photoemission Study of Heteroepitaxial AlGaN Films Grown on 6H-SiC", <u>Applied Surface Science</u> , 104/105, 455-460, (1996)
	Bermudez, V., et al., "The Growth and Properties of Al and AlN Films on GaN(0001)-(1 x 1)", <u>J. Applied Physics</u> , 79, 110-119, (Jan. 1996)
	Casey, H., et al., "Low Interface Trap Density for Remote Plasma Deposited SiO2 on n-type GaN", <u>Applied Phys. Lett.</u> , 68, 1850-1852, (March 1996)
	Chang, C., et al., "Novel Passivation Dielectrics-The Boron- or Phosphorus-Doped Hydrogenated Amorphous Silicon Carbide Films", <u>Journal of the Electrochemical Society</u> , 132, 418-422, (Feb. 1985)
	Choi, J., et al., "Effect of Deposition Conditions and Pretreatments on the Microstructure of MPECVD Diamond Thin Films", <u>Materials Chemistry and Physics</u> , 45, 176-179, (1996)
	Clarke, G., et al., "The Infrared Properties of Magnetron-Sputtered Diamond-Like Thin Films", <u>Thin Solid Films</u> , 280, 130-135, (1996)
	Compagnini, G., et al., "Spectroscopic Characterization of Annealed Si(1-x)C(x) Films", <u>J. Materials Res.</u> , 11, 2269-2273, (Sept. 1996)

Examiner	J. MANDT	Date Considered	11/05/02
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*Substitute Disclosure Statement Form (PTO-1449)

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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
InitialRECEIVED
AUG 26 2002
TECHNOLOGY CENTER 2800Dartnell, N., et al., "Reactive Ion Etching of Silicon Carbide (Si(x)C(1-x))", Vacuum, 46, 349-355, (1995)Demichelis, F., et al., "Influence of Doping on the Structural and Optoelectronic Properties of Amorphous and Microcrystalline Silicon Carbide", Journal of Applied Physics, 72, 1327-1333, (Aug. 15, 1992)Demichelis, F., et al., "Physical Properties of Undoped and Doped Microcrystalline SiC:H Deposited By PECVD", Materials Research Society Symposium Proceedings, 219, Anaheim, CA, 413-418, (4/30 - 5/3, 1991)Dipert, B., et al., "Flash Memory Goes Mainstream", IEEE Spectrum, 30, 48-52, (October 1993)Fissel, A., et al., "Epitaxial Growth of SiC Thin Films on Si-stabilized alpha-SiC (0001) at Low Temperatures by Solid-source Molecular Beam Epitaxy", Journal of Crystal Growth, 154, 72-80, (1995)Friedrichs, P., et al., "Interface Properties of Metal-Oxide-Semiconductor Structures on N-Type 6H and 4H-SiC", J. Applied Physics, 79, 7814-7819, (May 15, 1996)Fujii, T., et al., "Bonding Structures in Highly Photoconductive a-SiC:H Films Deposited by Hybrid-Plasma Chemical Vapor Deposition", Journal of Non-Crystalline Solids, 198-200, 577-581, (1996)Goetzberger, A., et al., Applied Solid State Science: Advances in Materials and Device Research, R. Wolfe, ed., Academic Press, New York, Including pg. 233, (1969)Graul, J., et al., "Growth Mechanism of Polycrystalline beta-SiC Layers on Silicon Substrate", Applied Phys. Lett., 21, 67-69, (July 1972)Hamakawa, Y., et al., "Optoelectronics and Photovoltaic Applications of Microcrystalline SiC", Materials Research Society Symposium Proceedings, 164, Boston, MA, 291-301, (11/29-12/1, 1989)He, Z., et al., "Ion-beam-assisted Deposition of Si-carbide Films", Thin Solid Films, 260, 32-37, (1995)

Examiner

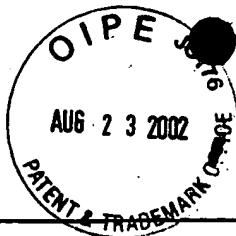
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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
InitialRECEIVED
AUG 26 2002
TECHNOLOGY CENTER 2800

[Handwritten initials] Hu, G., et al., "Will Flash Memory Replace Hard Disk Drive?", 1994 IEEE International Electron Device Meeting, Panel Discussion, Session 24, Outline, 2 pages, (Dec. 1994)

[Handwritten initials] Hwang, J., et al., "High Mobility beta-SiC Epilayer Prepared by Low-pressure Rapid Thermal Chemical Vapor Deposition on a (100) Silicon Substrate", Thin Solid Films, 272, 4-6, (1996)

[Handwritten initials] Jou, S., et al., "Electron Emission Characterization of Diamond Thin Films Grown from a Solid Carbon Source", Thin Solid Films, 280, 256-261, (1996)

[Handwritten initials] Kothandaraman, M., et al., "Reactive Ion Etching of Trenches in 6H-SiC", J. Electronic Materials, 25, 875-878, (1996)

[Handwritten initials] Kumbhar, A., et al., "Growth of Clean Amorphous Silicon-Carbon Alloy Films by Hot-Filament Assisted Chemical Vapor Deposition Technique", Applied Phys. Lett., 66, 1741-1743, (April 1995)

[Handwritten initials] Lakshmi, E., et al., "Interface-State Characteristics of GaN/GaAs MIS Capacitors", Solid-State Electronics, 25, 811-815, (1982)

[Handwritten initials] Lanois, F., et al., "Angle Etch Control for Silicon Carbide Power Devices", Applied Phys. Lett., 69, 236-238, (July 1996)

[Handwritten initials] Lau, S., et al., "Optoelectronic Properties of Highly Conductive Microcrystalline SiC Produced by Laser Crystallization of Amorphous SiC", J. of Non-Crystalline Solids, 198-200, 907-910, (1996)

[Handwritten initials] Leggieri, G., et al., "Laser Ablation Deposition of Silicon Carbide Films", Applied Surface Science, 96-98, 866-869, (1996)

[Handwritten initials] Lei, T., et al., "Epitaxial Growth and Characterization of Zinc-Blende Gallium Nitride on (001) Silicon", J. Appl. Phys., 71, 4933-4943, (May 1992)

[Handwritten initials] Liu, J., et al., "Formation of SiC Films on Silicon Field Emitters", Materials Res. Soc. Symp. Proc., 311, San Francisco, CA, (April 13-15, 1993)

[Handwritten initials] Liu, J., et al., "Modification of Si Field Emitter Surfaces by Chemical Conversion to SiC", J. Vac. Sci. Technology, B 12, 717-721, (1994)

[Handwritten initials] Luo, J., et al., "Localized Epitaxial Growth of Hexagonal and Cubic SiC Films on Si by Vacuum Annealing", Applied Phys. Lett., 69, 916-918, (Aug. 1996)

Examiner

J. MONDT *[Signature]*

Date Considered

11/05/02

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
Initial

[Signature] Martins, R., et al., "Transport Properties of Doped Silicon Oxycarbide Microcrystalline Films Produced by Spatial Separation Techniques", Solar Energy Materials and Solar Cells, 41-42, 493-517, (1996)

[Signature] Martins, R., et al., "Wide Band Gap Microcrystalline Silicon Thin Films", Diffusion and Defect Data : Solid State Phenomena, 44-46, Part 1, Scitec Publications, 299-346, (1995)

[Signature] Maury, F., et al., "Chemical Vapor Co-Deposition of C and SiC at Moderate Temperature for the Synthesis of Compositionally Modulated Si(x)C(1-x) Ceramic Layers", Surface and Coatings Technology, 76-77, 119-125, (1995)

[Signature] McLane, G., et al., "High Etch Rates of SiC in Magnetron Enhanced SF(6) Plasmas", Applied Phys. Lett., 68, 3755-3757, (June 1996)

[Signature] Mogab, C., et al., "Conversion of Si to Epitaxial SiC by Reaction with C(2)H(2)", J. Applied Physics, 45, 1075-1084, (March 1974)

[Signature] Molnar, R., et al., "Growth of Gallium Nitride by Electron-Cyclotron Resonance Plasma-Assisted Molecular-Beam Epitaxy: The Role of Charged Species", J. Appl. Phys., 76, 4587-4595, (1994)

[Signature] Muller, K., et al., "Trench Storage Node Technology for Gigabit DRAM Generations", Digest IEEE International Electron Devices Meeting, San Francisco, CA, 507-510, (Dec. 1996)

[Signature] Nemanich, P., et al., "Diamond Negative Electron Affinity Surfaces, Structures and Devices", Proc. : Third International Conference on Applications of Diamond Films and Related Materials, 1, Gaithersburg, MD, 17-24, (1995)

[Signature] Nemanich, R., et al., "Negative Electron Affinity Surfaces of Aluminum Nitride and Diamond", Diamond and Related Materials, 5, 790-796, (1996)

[Signature] Ouyang, M., et al., "Deposition of Diamond-Like Carbon Films via Excimer Laser Ablation of Polybutadiene", Materials Science and Engineering, B39, 228-231, (1996)

[Signature] Pankove, J., "Photoelectric Emission", In: Optical Processes in Semiconductors, Dover Publications Inc., New York, 287-301, (1971)

Examiner

J. MONDT

Date Considered

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*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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InitialRECEIVED
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TECHNOLOGY CENTER 2800Pankove, J., et al., "Photoemission from GaN", Applied Phys. Lett. 25, 53-55, (1974)Papadas, C., et al., "Modeling of the Intrinsic Retention Characteristics of FLOTOX EEPROM Cells Under Elevated Temperature Conditions", IEEE Transaction on Electron Devices, 42, 678-682, (April 1995)Patuwathavithane, C., et al., "Oxidation Studies for 6H-SiC", Proc. 4th Int. Conf. on Amorphous and Crystalline Silicon Carbide IV, Santa Clara, CA, 163-169, (Oct. 9-11, 1991)Pereyra, I., et al., "Wide Gap a-Si(1-x)C(x): H Thin Films Obtained Under Starving Plasma Deposition Conditions", J. Non-Crystalline Solids, 201, 110-118, (1996)Pollack, S., "Electron Transport Through Insulating Thin Films", Appl. Solid-State Science, 1, 345-355, (1969)Prendergast, J., "FLASH or DRAM: Memory Choice for the Future", IEEE Electron Device Meeting, Session 25, Phoenix, AZ, (1995)Rahman, M., et al., "Preparation and Electrical Properties of An Amorphous SiC/ Crystalline Si p(+)n Heterostructure", Japanese J. Applied Physics, 23, 515-524, (May 1984)Renlund, G., et al., "Silicon Oxycarbide Glasses: Part I. Preparation and Chemistry", Journal of Materials Research, 6, 2716-2722, (December 1991)Renlund, G., et al., "Silicon Oxycarbide Glasses: Part II. Structure and Properties", Journal of Materials Research, 6, 2723-2734, (December 1991)Sakata, I., et al., "Amorphous Silicon/Amorphous Silicon Carbide Heterojunctions Applied to Memory Device Structures", Electronics Letters, 30(9), 688-689, (1994)Schmidt, I., et al., "Low Temperature Diamond Growth Using Fluorinated Hydrocarbons", Diamond and Related Materials, 5, 1318-1322, (1996)Serre, C., et al., "Ion-Beam Synthesis of Amorphous SiC Films: Structural Analysis and Recrystallization", J. Appl. Phys., 72, 6907-6913, (May 1996)

Examiner

J. MONDT

Date Considered

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*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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Atty. Docket No.: 303.324US4

Serial No. Unknown

Applicant: Leonard Forbes et al.

Filing Date: Herewith

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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
InitialRECEIVED
AUG 26 2002
TECHNOLOGY CENTER 2850

- Sim, S., et al., "A New Planar Stacked Technology (PST) for Scalable and Embedded DRAMs", Digest IEEE Int. Electron Devices Meeting, San Francisco, CA, 504-507, (Dec. 1996)
- Suzaki, Y., et al., "Quantum Size Effects of a-Si(:H)/a-SiC(:H) Multilayer Films Prepared by rf Sputtering", Abstracts of Papers Published in the Int. J. Japanese Soc. for Precision Engineering, 28, Abstract of Paper in vol. 60, 182, (June 1994)
- Svirikova, N., et al., "Deposition Conditions and Density-of-States Spectrum of a-Si(1-x)C(x) :H Films Obtained by Sputtering", Semiconductors, 28, 1164-1169, (Dec. 1994)
- Sze, S., Physics of Semiconductors, 2nd Edition., John Wiley & Sons, Pub., New York, ISBN 0471056618, (1981)
- Sze, S.M., In: Physics of Semiconductor Devices, Wiley-Interscience, New York, p. 496-497, (1969)
- Tarui, Y., "Flash Memory Features Simple Structure, Superior Integration", JEE, 30, 84-87, (Sept. 1993)
- Tenhover, M., et al., "DC-Magnetron Sputtered Silicon Carbide", Materials Res. Soc. Symp. Proc., 356, Boston, MA, 227-232, (11/28-12/02, 1994)
- Thomas, J., et al., "Plasma Etching and Surface Analysis of a-SiC :H Films Deposited by Low Temperature Plasma Enhanced Chemical Vapor Deposition", Materials Res. Soc. Symp. Proc., 334, Boston, MA, 445-450, (11/29-12/02, 1993)
- Tiwari, S., et al., "A silicon nanocrystal based memory", Appl. Physics Lett., 68, 1377-1379, (1996)
- Tiwari, S., et al., "Volatile and Non-Volatile Memories in Silicon with Nano-Crystal Storage", Int'l Electron Devices Meeting: Technical Digest, Washington, DC, 521-524, (Dec. 1995)
- Tucker, C., et al., "Ion-beam-assisted Deposition of Nonhydrogenated a-Si:C Films", Can. J. Physics, 74, 97-101, (1996)

Examiner

J. MONDT

Date Considered

11/05/02

*Substitute Disclosure Statement Form (PTO-1516)

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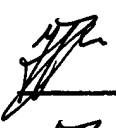
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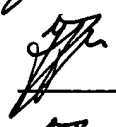
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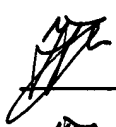
**Examiner
Initial


 van der Weide, J., et al., "Negative-electron-affinity Effects on the Diamond (100) Surface", Physical Review B [Condensed Matter], 50, 5803-5806, (Aug. 15, 1994)


 Vodakov, Y., et al., "Diffusion and Solubility of Impurities in Silicon Carbide", In: Silicon Carbide, R.C. Marshall, et al., eds., Univ. of South Carolina Press, 508-519, (1973)


 Wahab, Q., et al., "3C-SiC / Si / 3C-SiC Epitaxial Trilayer Films Deposited on Si (111) Substrates by Reactive Magnetron Sputtering", J. Materials Res., 10, 1349-1351, (June 1995)


 Watanabe, A., et al., "SiC Thin Film Preparation by ArF Excimer Laser Chemical Vapor Deposition. Part 1: Rate of Photolysis of Alkylsilanes by ArF Excimer Laser and their Decomposition Products", Thin Solid Films, 274, 70-75, (1996)

 Wolter, S., et al., "Textured Growth of Diamond on Silicon via in situ Carburization and Bias-Enhanced Nucleation", Appl. Phys. Lett., 62, 1215-1217, (March 1993)

 Wu, K., et al., "The Growth and Characterization of Silicon/Silicon Carbide Heteroepitaxial Films on Silicon Substrates by Rapid Thermal Chemical Vapor Deposition", Japanese J. Appl. Phys., 35, 3836-3840, (1996)

 Yamaguchi, Y., et al., "Properties of Heteroepitaxial 3C-SiC Films Grown by LPCVD", Digest of Tech. Papers: 8th Int. Conf. on Solid-State Sensors and Actuators and Eurosensors IX, vol. 2, Stockholm, Sweden, 190-193, (June 1995)

 Yamanashi, H., et al., "Deposition of Silicon Compound Thin Films in DC Discharge Plasma Using Hydrogen-Hexamethyldisilane Gas Mixture", Proc.: Int. Symp. on Surfaces and Thin Films of Electronic Materials. Bull. of the Res. Institute of Electronics, Shizuoka University, 30, 95-98, (1995)

 Yee, A., et al., "The Effect of Nitrogen on Pulsed Laser Deposition of Amorphous Silicon Carbide Films: Properties and Structure", J. Materials Research, 11, 1979-1986, (1996)

Examiner

J. MONDT

Date Considered

11/05/02

*Substitute Disclosure Statement Form (PTO-144)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner
InitialRECEIVED
AUG 26 2002
TECHNOLOGY CENTER 2900

[Signature] Yoder, M., "Wide Bandgap Semiconductor Materials and Devices", IEEE
Transactions on Electron Devices, 43, 1633-1636, (October 1996)

Examiner <u>J. MONDT</u> <i>[Signature]</i>	Date Considered <u>11/05/02</u>
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Complete if Known

Application Number	09/691004
Filing Date	October 18, 2000
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Unknown

Attorney Docket No: 00303.324US4

Sheet 1 of 1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
<i>[Signature]</i>	US-3792465	02/12/1974	Collins, D. R., et al	340	324 R	12/30/1971
<i>[Signature]</i>	US-6130147	10/10/2000	Major, J. S., et al	438	604	03/18/1997

FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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<i>[Signature]</i>		BURNS, S.G., et al., In: <u>Principles of Electronic Circuits</u> , West Publishing Co., St. Paul, MN, (1987), 382-383	
<i>[Signature]</i>		BURNS, S., et al., In: <u>Principles of Electronic Circuits</u> , West Publishing Company, (1987), pg. 380	
<i>[Signature]</i>		CAPASSO, F., et al., "New Floating-Gate AlGaAs/GaAs Memory Devices with Graded-Gad Electron Injector and Long Retention Times", <u>IEEE Electron Device Letters</u> , (1988), pp. 377-379	
<i>[Signature]</i>		NG, K., In: <u>Complete Guide To Semiconductor Devices</u> , McGraw-Hill, Inc. New York, (1995), pp. 322-328, 605-608	
<i>[Signature]</i>		WOLF, S., "Semiconductor Memory Process Integration", <u>Silicon Processing for The VLSI Era, Volume 2: Process Integration</u> , (1990), pp. 623-628	

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